

IEEE Honors Mark Rodwell for His Work in High Frequency Electronics



UCSB researcher [Mark Rodwell](#) has been honored by the [Institute of Electrical and Electronics Engineers](#) (IEEE) for his work on high-frequency electronics.

Rodwell, a professor in the [Electrical and Computer Engineering Department](#), and head of the [UCSB Nanofabrication Facility](#), is the recipient of the 2010 [David Sarnoff Award](#). This is the second time in four years that a faculty member in the department has picked up the prize, which recognizes exceptional contributions to electronics.

Rodwell's research focuses on very-high-frequency transistors and integrated circuits. The IEEE is honoring him for developing indium phosphide-based bipolar transistors and integrated circuits for millimeter-wave and sub-millimeter-wave applications.

Rodwell, who was elected a fellow of IEEE in 2003, came to UCSB in 1998. He earned a Ph.D. in Electrical Engineering from Stanford University and earlier worked at AT&T Bell Laboratories.

The David Sarnoff Award was established in 1959 under an agreement between the RCA Corporation-now Sarnoff-and the American Institute of Electrical Engineers-now IEEE. [Umesh Mishra](#), a colleague of Rodwell's in the Electrical and Computer Engineering Department, received the award in 2007 for the development of gallium nitride electronics.

Rodwell will receive the 2010 award, which includes an honorarium, at the IEEE Honors Ceremony, to be held on June 26 in Montreal, Canada.

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Related Links

[IEEE David Sarnoff Award](#)

[Rodwell's High Frequency Electronics Group](#)

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